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(54) Title: SEMICONDUCTOR PROFILE MEASUREMENT BASED ON A SCANNING CONDITIONAL MODEL

(57) Abstract: Methods and systems for measuring semiconductor structures based on a trained scanning conditional measurement model are described herein. A scanning conditional model is trained based on Design Of Experiments (DOE) measurement data associated with known values of one or more parameters of interest and a set of perturbed values of the one or more parameters of interest. The trained conditional model minimizes the output of an error function characterizing the error between the known values of the perturbed values of the one or more parameters of interest for the given DOE measurement data. During inference, an error value associated with each candidate value of one or more parameters of interest is determined by the trained scanning conditional measurement model. The estimated value of the parameter of interest is the candidate value of the parameter of interest associated with the minimum error value.

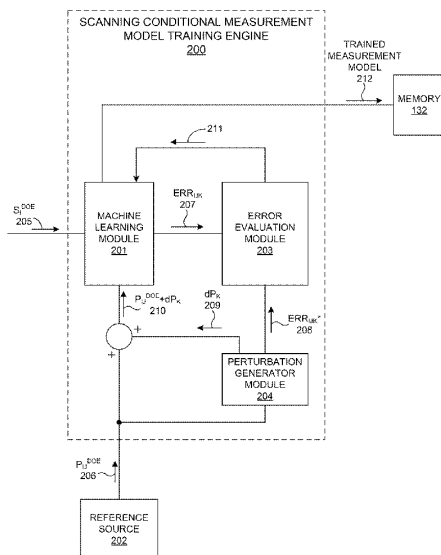


FIG. 2

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